

## General Description

The WSR80N10 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSR80N10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

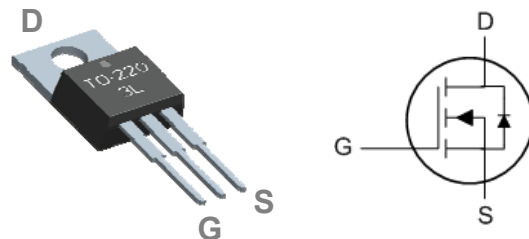
## Product Summary

$BV_{DSS}$	$R_{DSON}$	$I_D$
100V	10mΩ	85A

## Applications

- Power Management in TV Converter.
- DC-DC Converter
- LED TV Back Light

## TO-220AB Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	±25	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	85	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	65	A
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	10	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	8.2	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup> , $T_C=25^{\circ}C$	200	A
EAS	Avalanche Energy, Single pulse, $L=0.5mH$	189	mJ
$I_{AS}$	Avalanche Current, Single pulse, $L=0.5mH$	28	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation <sup>4</sup>	150	W
$P_D@T_C=100^{\circ}C$	Total Power Dissipation <sup>4</sup>	75	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	50	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	1.1	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.096	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	10	13	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	2.0	3.0	4.0	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.5	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =30A	---	27	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.0	1.8	Ω
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =80V, V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	42	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	12	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	12	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =50V, V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω, I <sub>D</sub> =1A	---	19	---	ns
T <sub>r</sub>	Rise Time		---	9	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	36	---	
T <sub>f</sub>	Fall Time		---	22	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	2100	---	pF
C <sub>oss</sub>	Output Capacitance		---	255	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	100	---	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	V <sub>DD</sub> =25V, L=0.5mH, I <sub>AS</sub> =28A	160	---	---	mJ

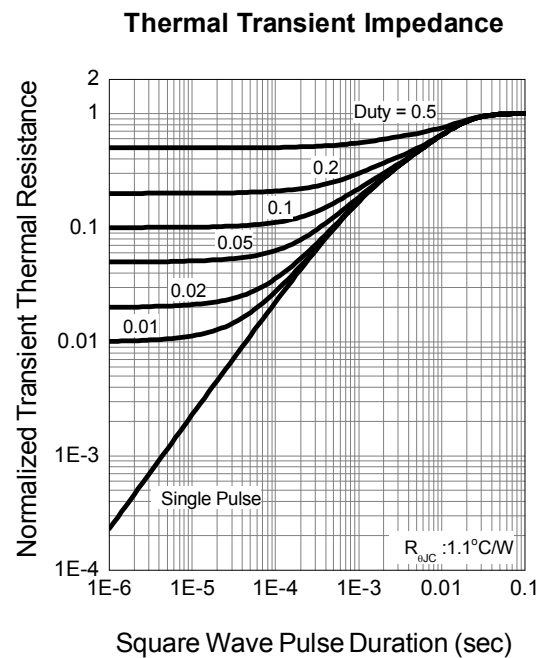
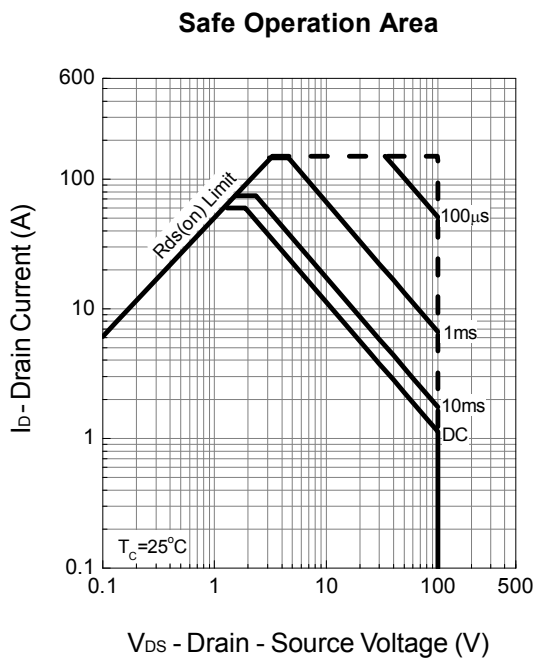
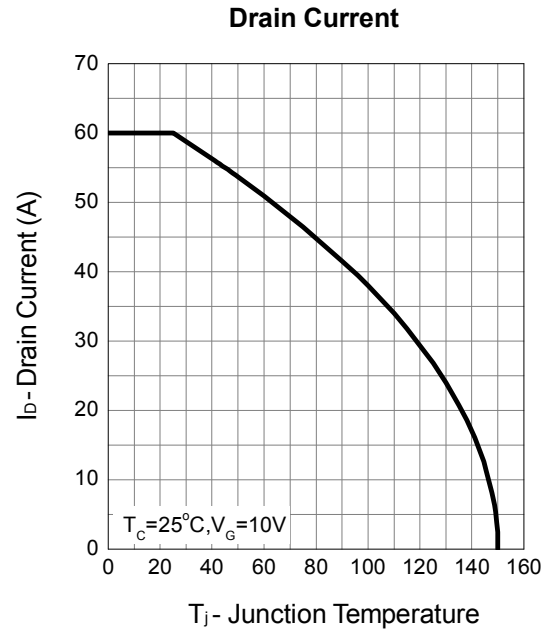
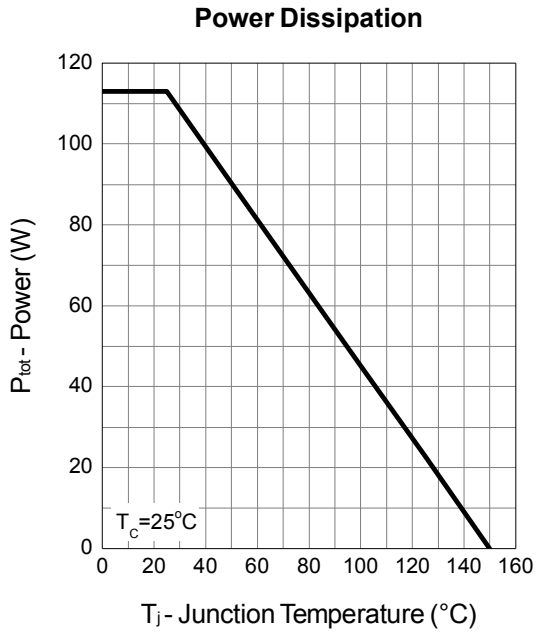
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	35	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>		---	---	60	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =15A, T <sub>J</sub> =25°C	---	---	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =15A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	42	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	90	---	nC

Note :

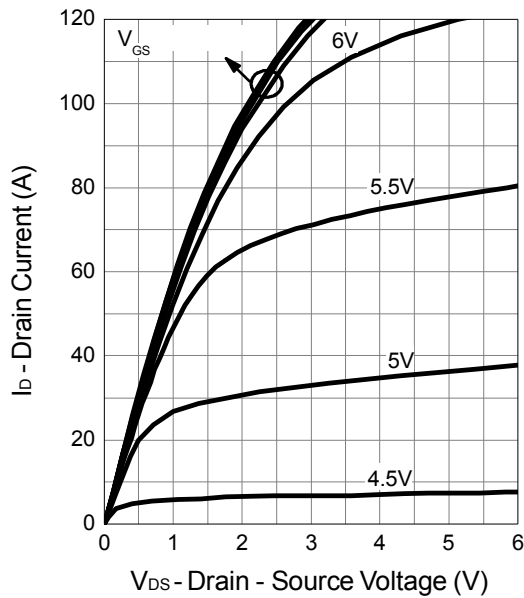
- The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper, t<10sec.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V<sub>DS</sub>=25V, V<sub>GS</sub>=10V, L=0.5mH, I<sub>AS</sub>=26A
- The power dissipation is limited by 150°C junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

**Typical Operating Characteristics**

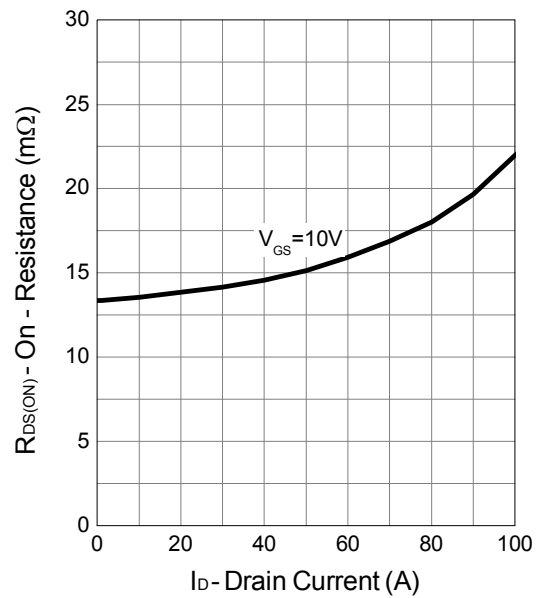


**Typical Operating Characteristics (Cont.)**

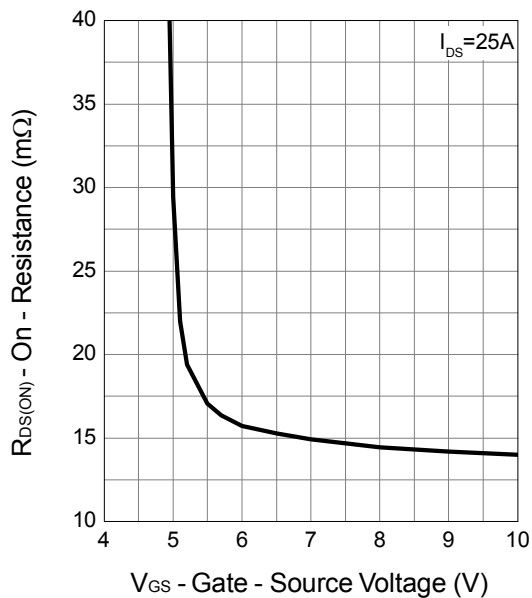
**Output Characteristics**



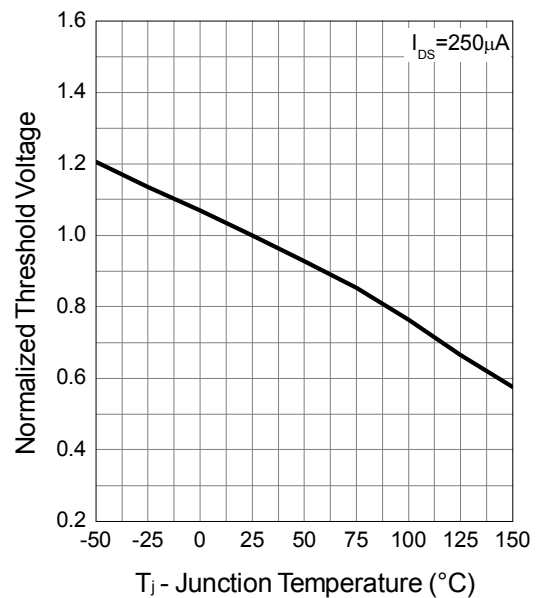
**Drain-Source On Resistance**



**Gate-Source On Resistance**

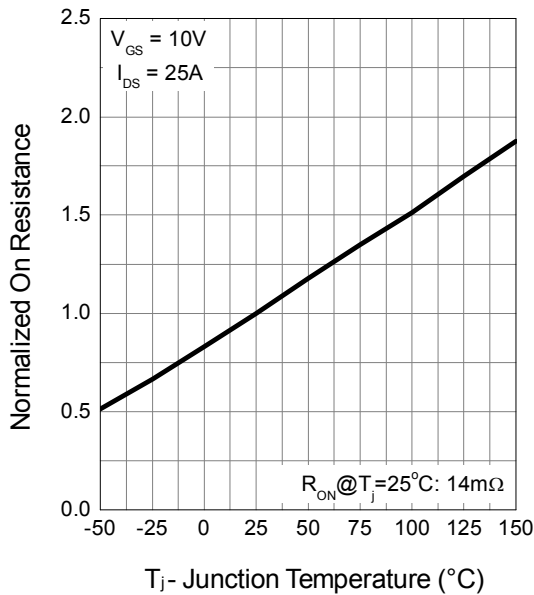


**Gate Threshold Voltage**

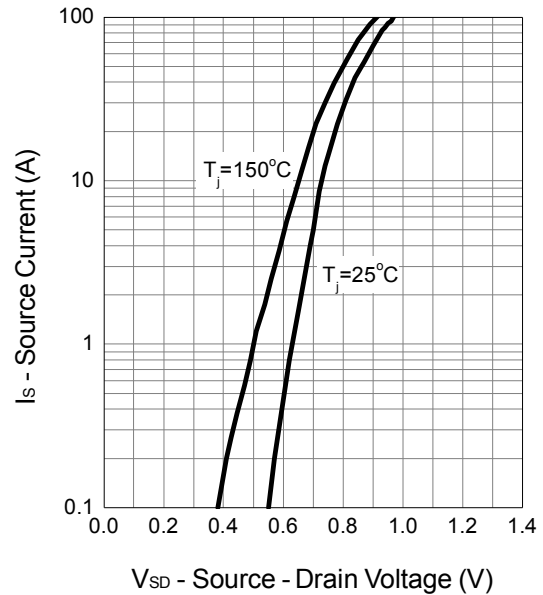


**Typical Operating Characteristics (Cont.)**

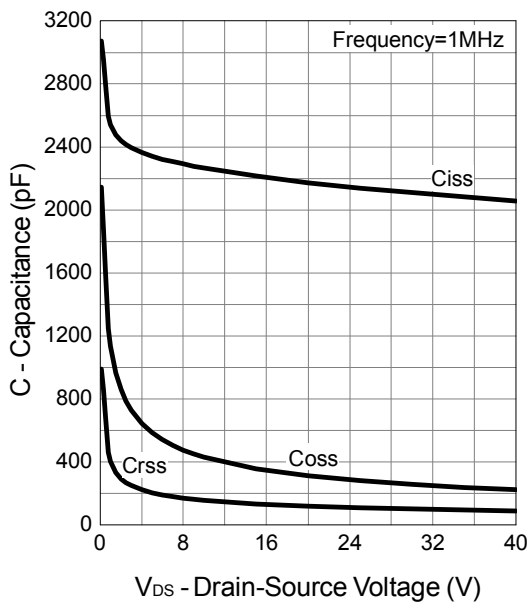
**Drain-Source On Resistance**



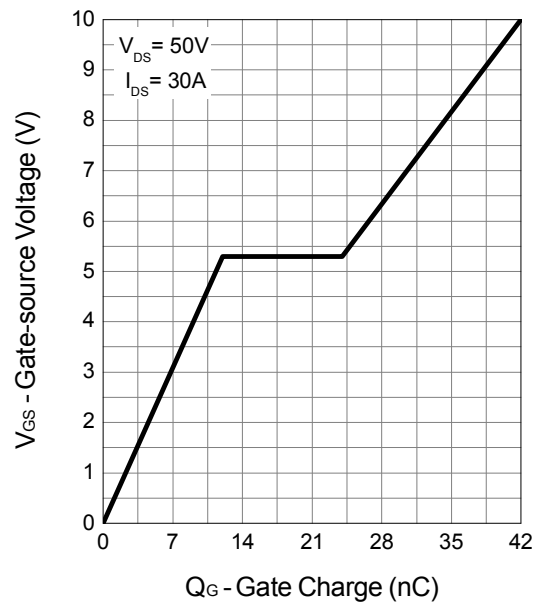
**Source-Drain Diode Forward**



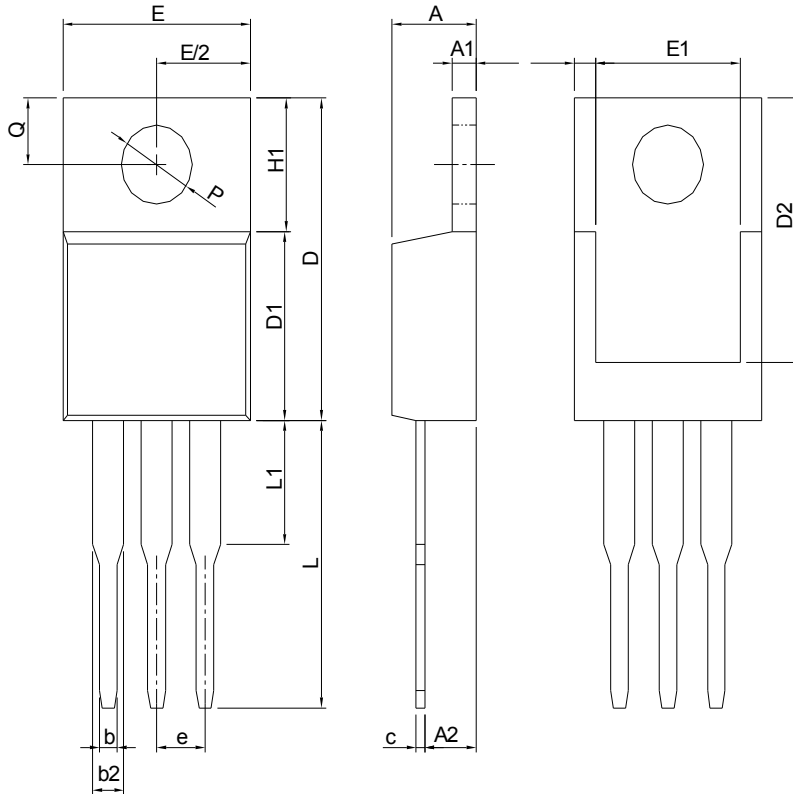
**Capacitance**



**Gate Charge**

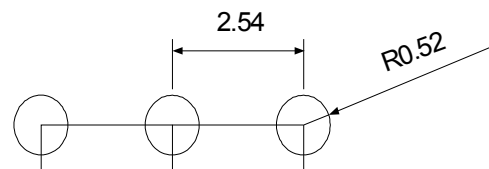


**Package Information TO-220AB**



DIMENSIONS	TO-220			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	3.56	4.83	0.140	0.190
A1	0.51	1.40	0.020	0.055
A2	2.03	2.92	0.080	0.115
b	0.38	1.02	0.015	0.040
b2	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.22	16.51	0.560	0.650
D1	8.38	9.02	0.330	0.355
D2	12.19	13.65	0.480	0.537
E	9.65	10.67	0.380	0.420
E1	6.86	8.89	0.270	0.350
e	2.54 BSC		0.100 BSC	
H1	5.84	6.86	0.230	0.270
L	12.70	14.73	0.500	0.580
L1		6.35		0.250
P	3.53	4.09	0.139	0.161
Q	2.54	3.43	0.100	0.135

**RECOMMENDED LAND PATTERN**



UNIT: mm

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